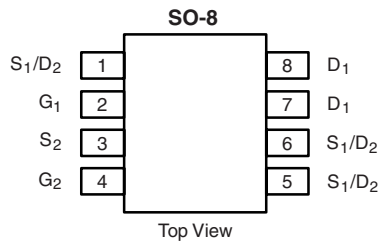


Dual N-Channel 30-V (D-S) MOSFET with Schottky Diode

PRODUCT SUMMARY				
	V _{DS} (V)	R _{DS(on)} (Ω)	I _D (A) ^{a, e}	Q _g (Typ.)
Channel-1	30	0.018 at V _{GS} = 10 V	8.0	10.5
		0.022 at V _{GS} = 4.5 V	8.0	
Channel-2	30	0.018 at V _{GS} = 10 V	8.0	10.5
		0.022 at V _{GS} = 4.5 V	8.0	

SCHOTTKY PRODUCT SUMMARY		
V _{DS} (V)	V _{SD} (V) Diode Forward Voltage	I _F (A) ^a
30	0.43 V at 1.0 A	2.8



Ordering Information: Si4650DY-T1-E3 (Lead (Pb)-free)
Si4650DY-T1-GE3 (Lead (Pb)-free and Halogen-free)

FEATURES

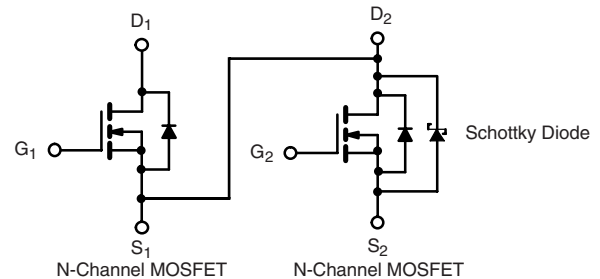
- Halogen-free According to IEC 61249-2-21 Definition
- TrenchFET[®] Power MOSFET
- 100 % R_g and UIS Tested
- Compliant to RoHS Directive 2002/95/EC



RoHS
COMPLIANT
HALOGEN
FREE
Available

APPLICATIONS

- Notebook Logic dc-to-dc
- Low Current dc-to-dc



ABSOLUTE MAXIMUM RATINGS T _A = 25 °C, unless otherwise noted				
Parameter	Symbol	Channel-1	Channel-2	Unit
Drain-Source Voltage	V _{DS}	30	30	V
Gate-Source Voltage	V _{GS}	± 20	± 20	V
Continuous Drain Current (T _J = 150 °C)	I _D	T _C = 25 °C	8.0 ^e	8.0 ^e
		T _C = 70 °C	7.8	7.8
		T _A = 25 °C	7.8 ^{b, c}	7.8 ^{b, c}
		T _A = 70 °C	6.2 ^{b, c}	6.2 ^{b, c}
Pulsed Drain Current (10 μs Pulse Width)	I _{DM}	30	30	A
Source-Drain Current Diode Current	I _S	T _C = 25 °C	2.8	2.8
		T _A = 25 °C	1.8 ^{b, c}	1.8 ^{b, c}
Pulsed Source-Drain Current	I _{SM}	30	30	A
Single Pulse Avalanche Current	I _{AS}	20	20	A
Single Pulse Avalanche Energy	E _{AS}	20	20	mJ
Maximum Power Dissipation	P _D	T _C = 25 °C	3.1	3.1
		T _C = 70 °C	2	2
		T _A = 25 °C	2 ^{b, c}	2 ^{b, c}
		T _A = 70 °C	1.2 ^{b, c}	1.2 ^{b, c}
Operating Junction and Storage Temperature Range	T _J , T _{stg}	- 55 to 150		°C

THERMAL RESISTANCE RATINGS						
Parameter	Symbol	Channel-1		Channel-2		Unit
		Typ.	Max.	Typ.	Max.	
Maximum Junction-to-Ambient ^{b, d}	R _{thJA}	52	62.5	52	62.5	°C/W
Maximum Junction-to-Foot (Drain)	R _{thJF}	35	40	35	40	°C/W

Notes:

- Based on T_C = 25 °C.
- Surface mounted on 1" x 1" FR4 board.
- t = 10 s.
- Maximum under steady state conditions is 110 °C/W (Channel-1) and 110 °C/W (Channel-2).
- Package limited.

SPECIFICATIONS $T_J = 25^\circ\text{C}$, unless otherwise noted								
Parameter	Symbol	Test Conditions		Min.	Typ. ^a	Max.	Unit	
Static								
Drain-Source Breakdown Voltage	V_{DS}	$V_{GS} = 0\text{ V}, I_D = 1\text{ mA}$	Ch-1	30			V	
		$V_{GS} = 0\text{ V}, I_D = 1\text{ mA}$	Ch-2	30				
V_{DS} Temperature Coefficient	$\Delta V_{DS}/T_J$	$I_D = 250\ \mu\text{A}$	Ch-1		35		mV/ $^\circ\text{C}$	
$V_{GS(th)}$ Temperature Coefficient	$\Delta V_{GS(th)}/T_J$	$I_D = 250\ \mu\text{A}$	Ch-1		-6			
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 1\text{ mA}$	Ch-1	1		3	V	
		$V_{DS} = V_{GS}, I_D = 1\text{ mA}$	Ch-2	1		3		
Gate-Body Leakage	I_{GSS}	$V_{DS} = 0\text{ V}, V_{GS} = \pm 20\text{ V}$	Ch-1			100	μA	
		$V_{DS} = 0\text{ V}, V_{GS} = \pm 20\text{ V}$	Ch-2			100		
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = 30\text{ V}, V_{GS} = 0\text{ V}$	Ch-1			0.001	mA	
		$V_{DS} = 30\text{ V}, V_{GS} = 0\text{ V}$	Ch-2		0.06	0.5		
		$V_{DS} = 30\text{ V}, V_{GS} = 0\text{ V}, T_J = 100^\circ\text{C}$	Ch-1			0.025		
		$V_{DS} = 30\text{ V}, V_{GS} = 0\text{ V}, T_J = 100^\circ\text{C}$	Ch-2		5	20		
On-State Drain Current ^b	$I_{D(on)}$	$V_{DS} = 5\text{ V}, V_{GS} = 10\text{ V}$	Ch-1	20			A	
		$V_{DS} = 5\text{ V}, V_{GS} = 10\text{ V}$	Ch-2	20				
Drain-Source On-State Resistance ^b	$R_{DS(on)}$	$V_{GS} = 10\text{ V}, I_D = 8\text{ A}$	Ch-1		0.014	0.018	Ω	
		$V_{GS} = 10\text{ V}, I_D = 8\text{ A}$	Ch-2		0.014	0.018		
		$V_{GS} = 4.5\text{ V}, I_D = 5\text{ A}$	Ch-1		0.017	0.022		
		$V_{GS} = 4.5\text{ V}, I_D = 5\text{ A}$	Ch-2		0.017	0.022		
Forward Transconductance ^b	g_{fs}	$V_{DS} = 15\text{ V}, I_D = 8\text{ A}$	Ch-1		40		S	
		$V_{DS} = 15\text{ V}, I_D = 8\text{ A}$	Ch-2		40			
Dynamic^a								
Input Capacitance	C_{iss}	Channel-1 $V_{DS} = 15\text{ V}, V_{GS} = 0\text{ V}, f = 1\text{ MHz}$	Ch-1		1550		pF	
			Ch-2		1550			
Output Capacitance	C_{oss}		Ch-1		220			
			Ch-2		275			
Reverse Transfer Capacitance	C_{rss}	Channel-2 $V_{DS} = 15\text{ V}, V_{GS} = 0\text{ V}, f = 1\text{ MHz}$	Ch-1		80			
			Ch-2		80			
Total Gate Charge	Q_g		$V_{DS} = 15\text{ V}, V_{GS} = 10\text{ V}, I_D = 8\text{ A}$	Ch-1		25.5	40	nC
				Ch-2		25.5	40	
		$V_{DS} = 15\text{ V}, V_{GS} = 4.5\text{ V}, I_D = 8\text{ A}$	Ch-1		10.5	16		
			Ch-2		10.5	16		
Gate-Source Charge	Q_{gs}	Channel-2 $V_{DS} = 15\text{ V}, V_{GS} = 4.5\text{ V}, I_D = 8\text{ A}$	Ch-1		5			
Gate-Drain Charge	Q_{gd}		Ch-2		5			
Gate Resistance	R_g	$f = 1\text{ MHz}$	Ch-1		1.8	3.0	Ω	
			Ch-2		1.8	3.0		

Notes:

- a. Guaranteed by design, not subject to production testing.
b. Pulse test; pulse width $\leq 300\ \mu\text{s}$, duty cycle $\leq 2\%$.



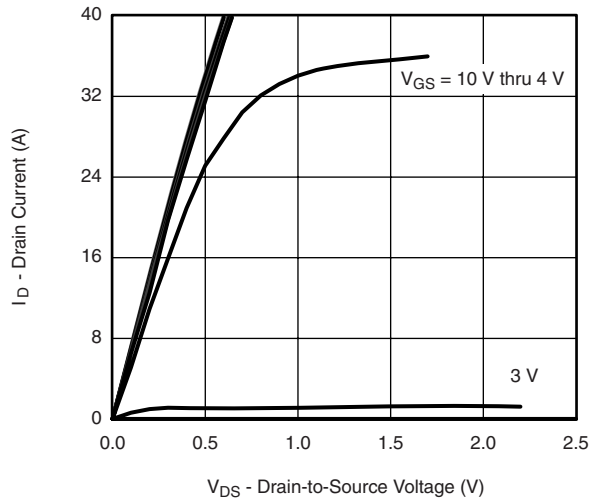
SPECIFICATIONS $T_J = 25\text{ }^\circ\text{C}$, unless otherwise noted							
Parameter	Symbol	Test Conditions	Min.	Typ. ^a	Max.	Unit	
Dynamic^a							
Turn-On Delay Time	$t_{d(on)}$	Channel-1 $V_{DD} = 15\text{ V}$, $R_L = 3\ \Omega$ $I_D \cong 5\text{ A}$, $V_{GEN} = 10\text{ V}$, $R_g = 1\ \Omega$	Ch-1		7	14	ns
			Ch-2		7	14	
Rise Time	t_r		Ch-1		29	45	
			Ch-2		29	45	
Turn-Off Delay Time	$t_{d(off)}$	Channel-2 $V_{DD} = 15\text{ V}$, $R_L = 3\ \Omega$ $I_D \cong 5\text{ A}$, $V_{GEN} = 10\text{ V}$, $R_g = 1\ \Omega$	Ch-1		19	30	
			Ch-2		19	30	
Fall Time	t_f		Ch-1		8	16	
			Ch-2		8	16	
Turn-On Delay Time	$t_{d(on)}$	Channel-1 $V_{DD} = 15\text{ V}$, $R_L = 3\ \Omega$ $I_D \cong 5\text{ A}$, $V_{GEN} = 4.5\text{ V}$, $R_g = 1\ \Omega$	Ch-1		32	50	
			Ch-2		32	50	
Rise Time	t_r		Ch-1		130	200	
			Ch-2		130	200	
Turn-Off Delay Time	$t_{d(off)}$	Channel-2 $V_{DD} = 15\text{ V}$, $R_L = 3\ \Omega$ $I_D \cong 5\text{ A}$, $V_{GEN} = 4.5\text{ V}$, $R_g = 1\ \Omega$	Ch-1		19	30	
			Ch-2		19	30	
Fall Time	t_f		Ch-1		34	55	
			Ch-2		34	55	
Drain-Source Body Diode Characteristics							
Continuous Source-Drain Diode Current	I_S	$T_C = 25\text{ }^\circ\text{C}$	Ch-1			2.8	A
			Ch-2			2.8	
Pulse Diode Forward Current ^a	I_{SM}		Ch-1			30	
			Ch-2			30	
Body Diode Voltage	V_{SD}	$I_S = 2\text{ A}$	Ch-1		0.77	1.1	V
		$I_S = 1\text{ A}$	Ch-2		0.37	0.43	
Body Diode Reverse Recovery Time	t_{rr}	Channel-1 $I_F = 4\text{ A}$, $dI/dt = 100\text{ A}/\mu\text{s}$, $T_J = 25\text{ }^\circ\text{C}$	Ch-1		25	40	ns
			Ch-2		23	40	
Body Diode Reverse Recovery Charge	Q_{rr}		Ch-1		18	30	nC
			Ch-2		13	20	
Reverse Recovery Fall Time	t_a	Channel-2 $I_F = 4\text{ A}$, $dI/dt = 100\text{ A}/\mu\text{s}$, $T_J = 25\text{ }^\circ\text{C}$	Ch-1		14		ns
			Ch-2		11		
Reverse Recovery Rise Time	t_b		Ch-1		11		
			Ch-2		12		

Notes:

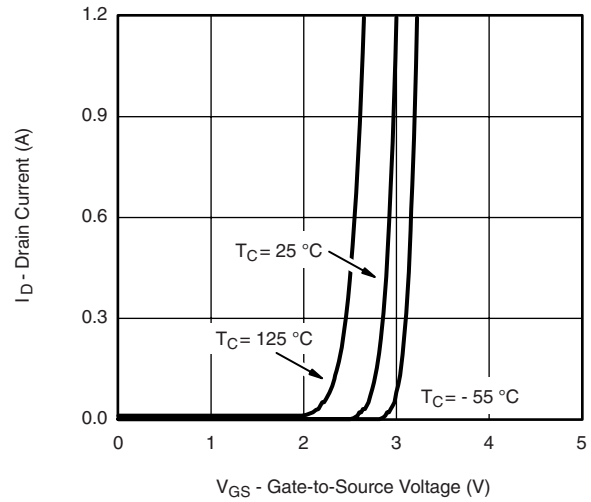
- a. Guaranteed by design, not subject to production testing.
- b. Pulse test; pulse width $\leq 300\ \mu\text{s}$, duty cycle $\leq 2\%$.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

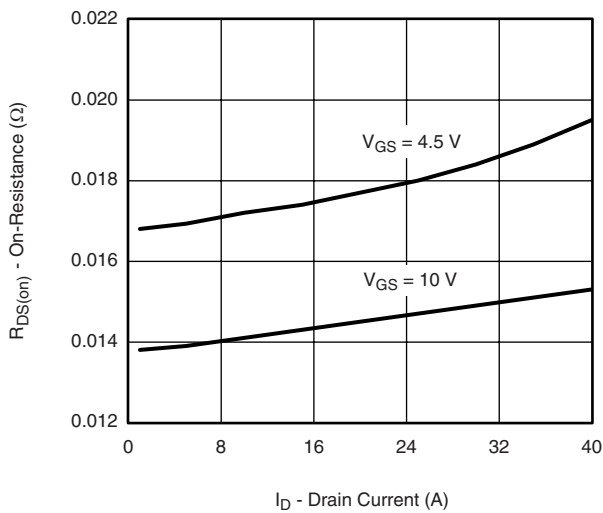
CHANNEL-1 TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



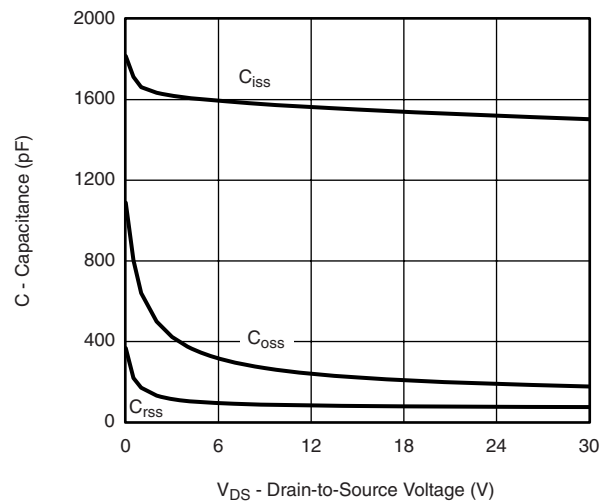
Output Characteristics



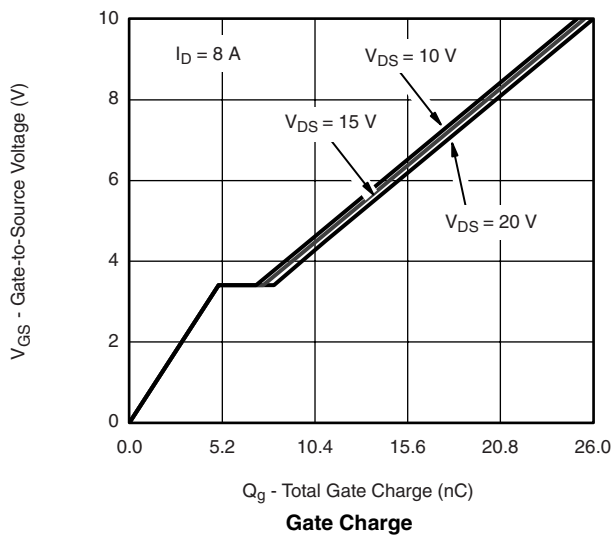
Transfer Characteristics



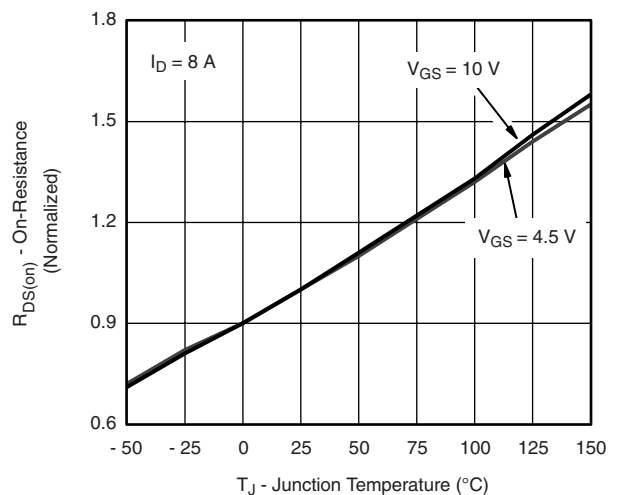
On-Resistance vs. Drain Current



Capacitance

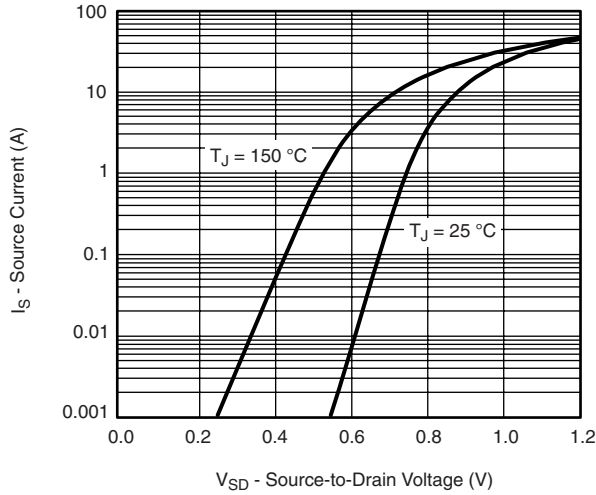


Gate Charge

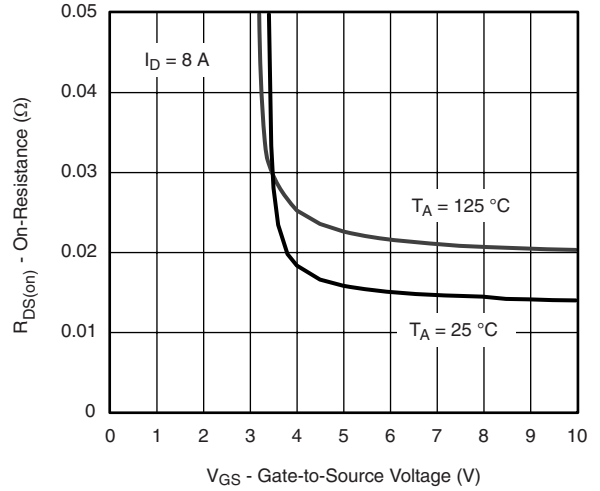


On-Resistance vs. Junction Temperature

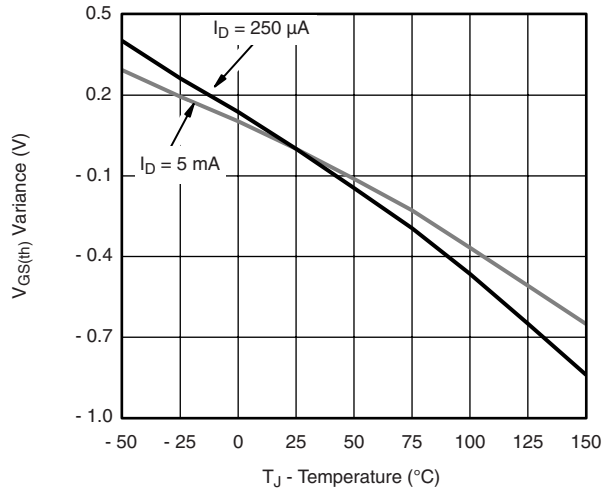
CHANNEL-1 TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



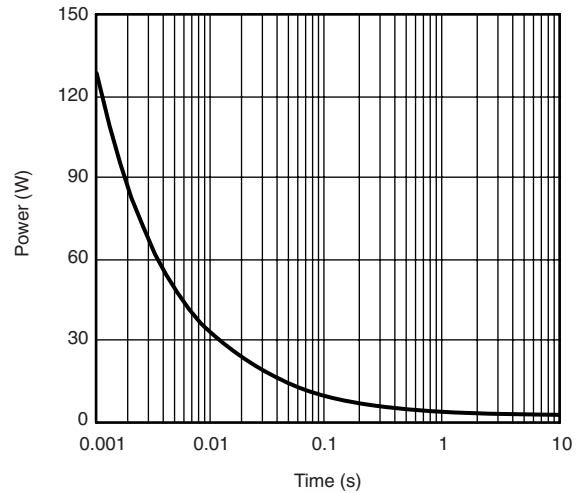
Source-Drain Diode Forward Voltage



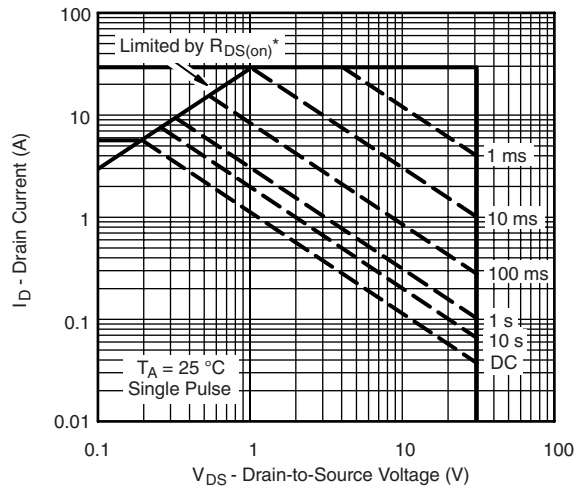
On-Resistance vs. Gate-to-Source Voltage



Threshold Voltage



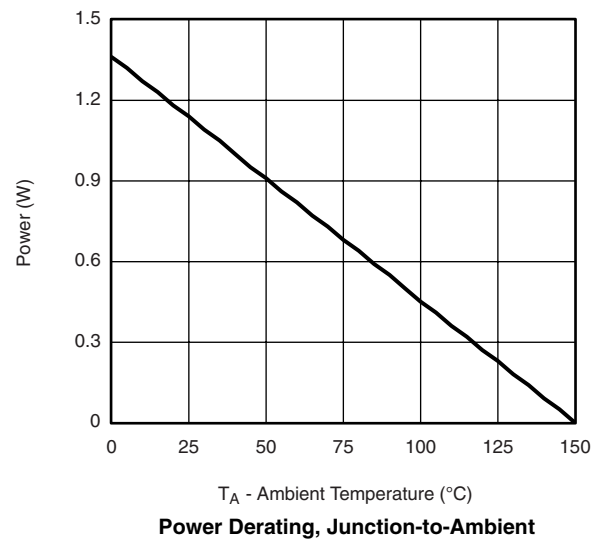
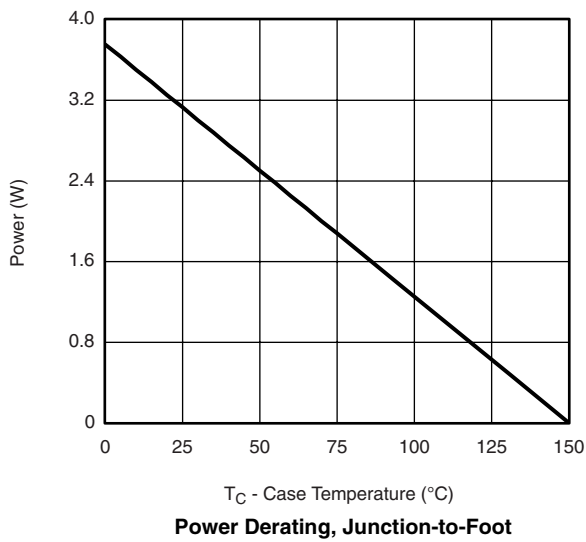
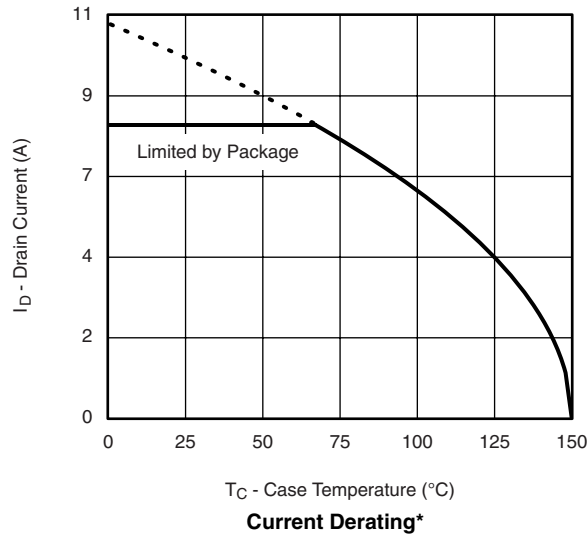
Single Pulse Power, Junction-to-Ambient



* $V_{GS} >$ minimum V_{GS} at which $R_{DS(on)}$ is specified

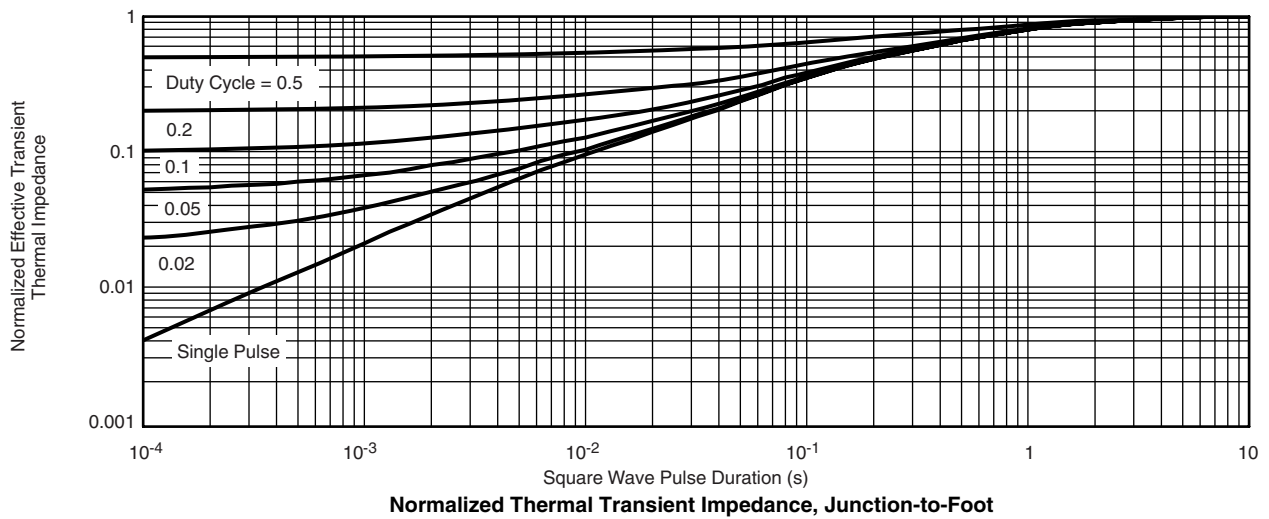
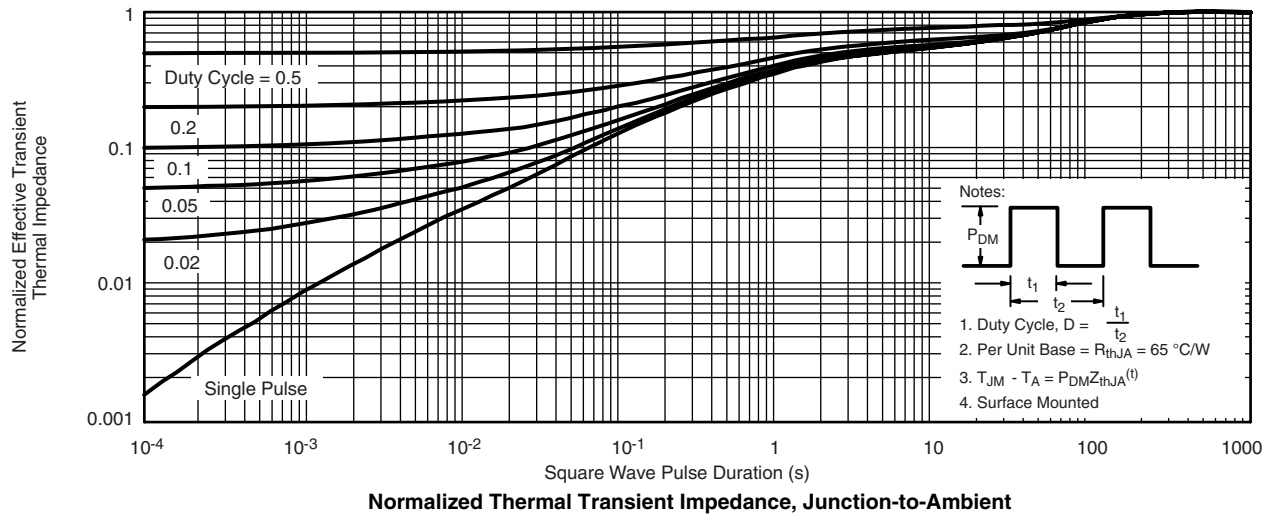
Safe Operating Area, Junction-to-Ambient

CHANNEL-1 TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted

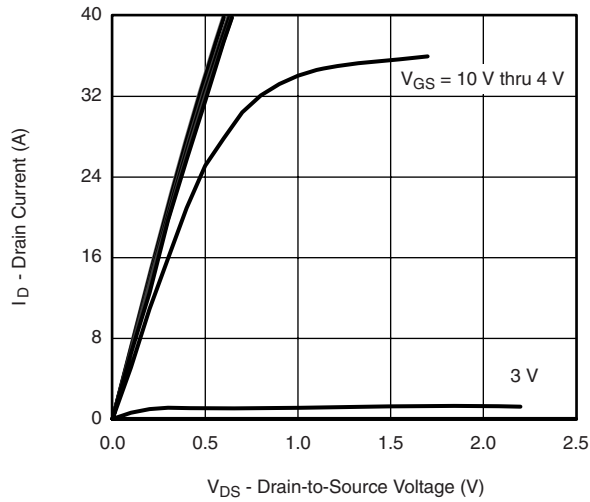


* The power dissipation P_D is based on $T_{J(max)} = 150$ °C, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit.

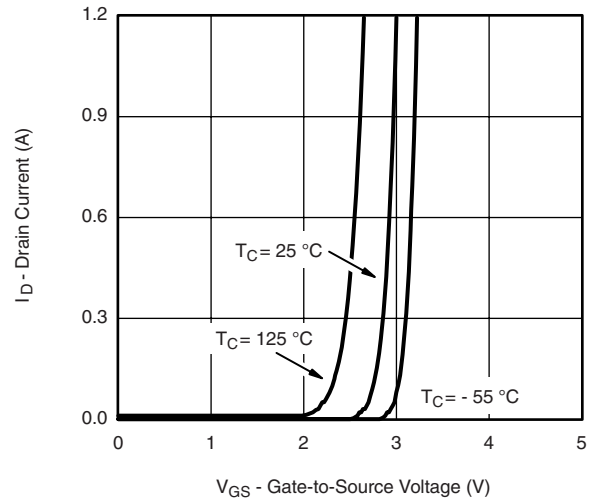
CHANNEL-1 TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



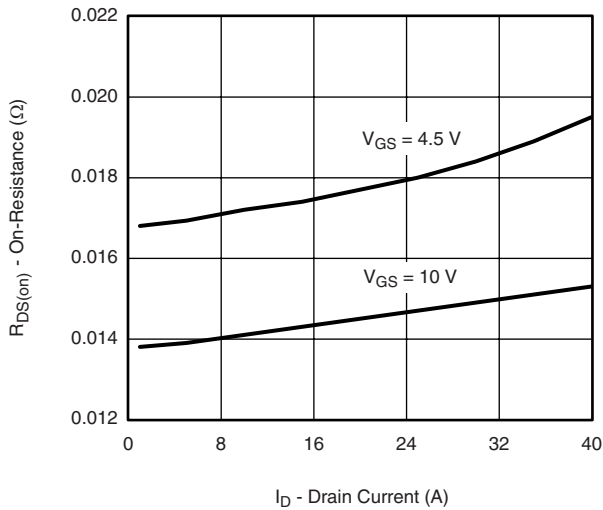
CHANNEL-2 TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



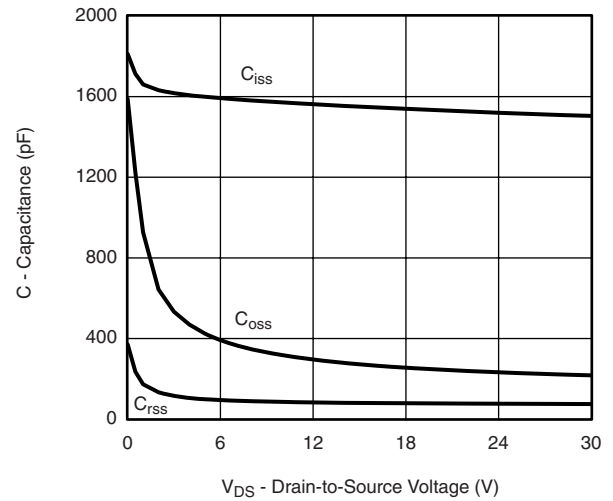
Output Characteristics



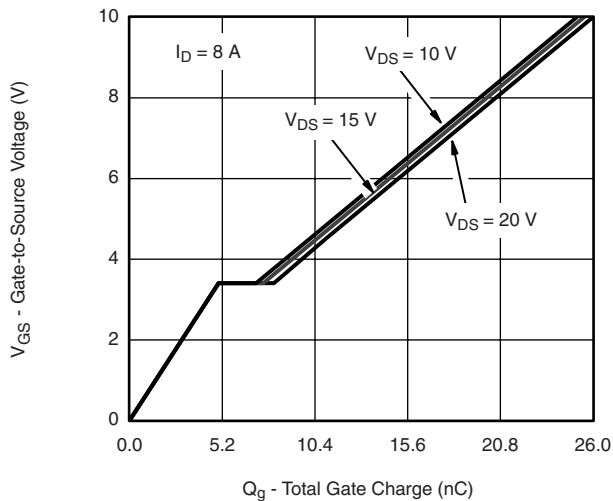
Transfer Characteristics



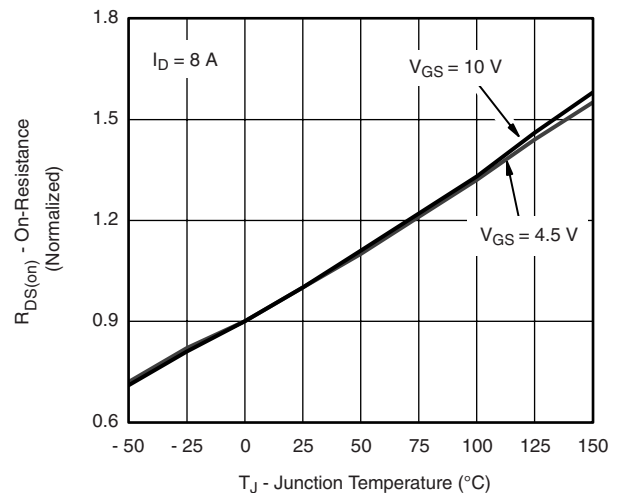
On-Resistance vs. Drain Current



Capacitance

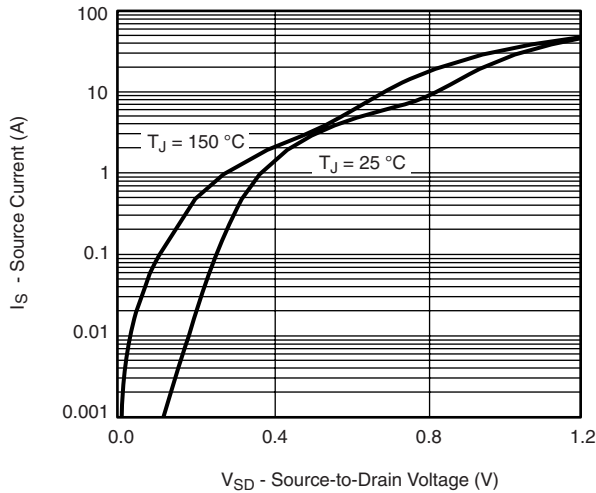


Gate Charge

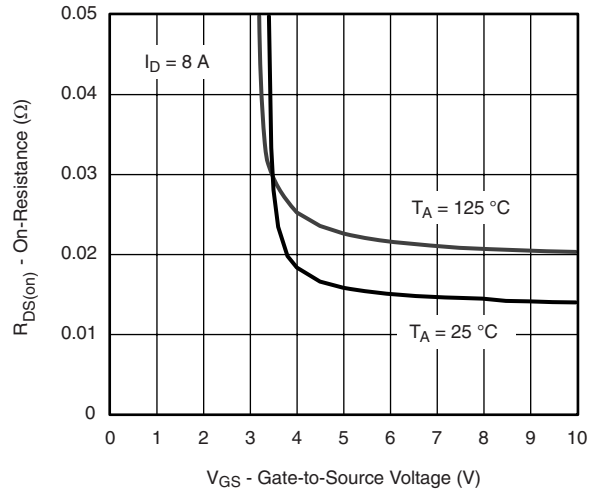


On-Resistance vs. Junction Temperature

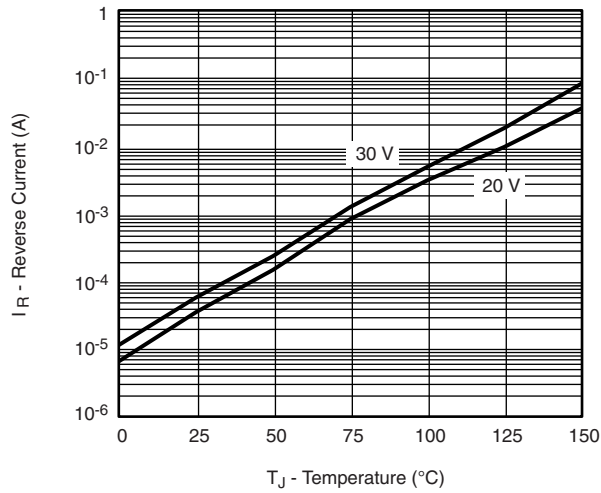
CHANNEL-2 TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



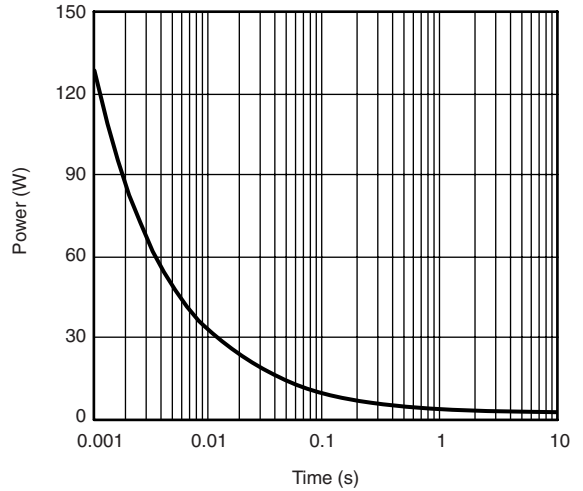
Source-Drain Diode Forward Voltage



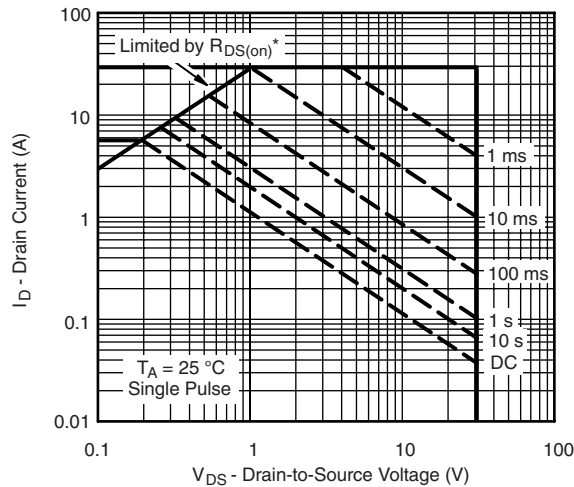
On-Resistance vs. Gate-to-Source Voltage



Reverse Current



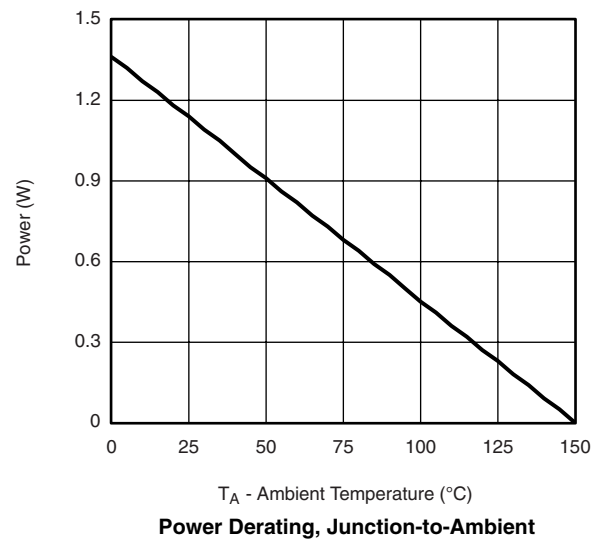
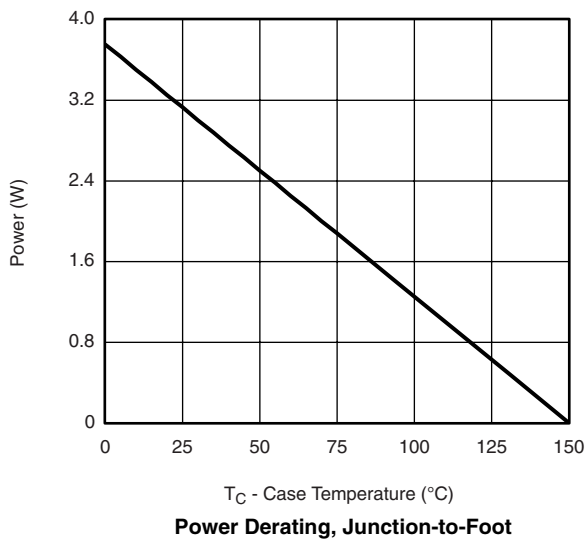
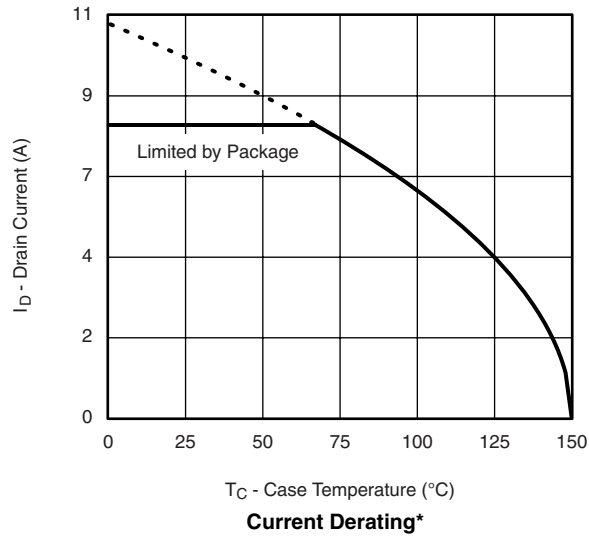
Single Pulse Power, Junction-to-Ambient



* $V_{GS} >$ minimum V_{GS} at which $R_{DS(on)}$ is specified

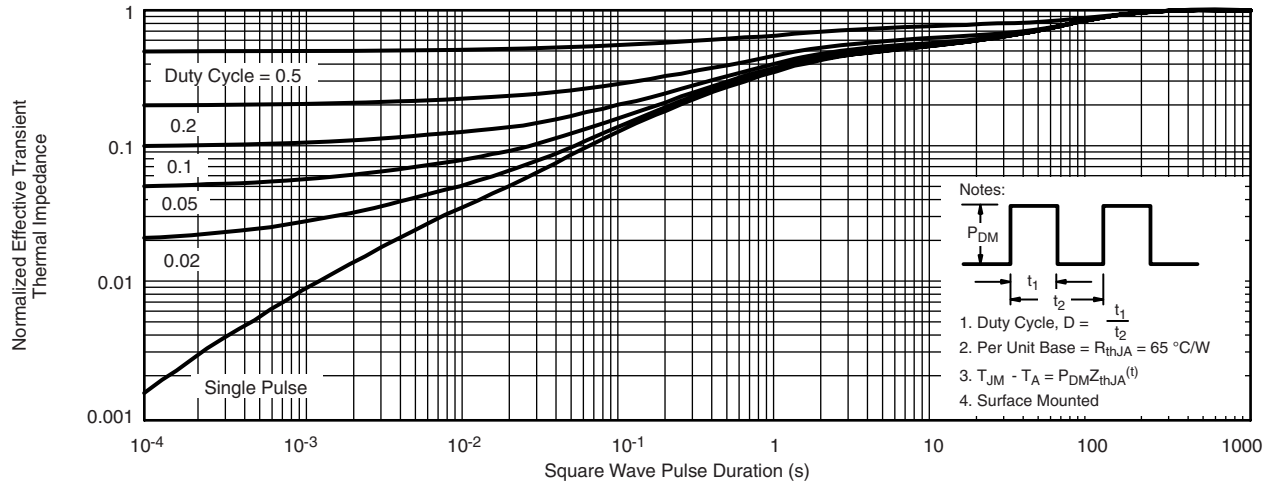
Safe Operating Area, Junction-to-Ambient

CHANNEL-2 TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted

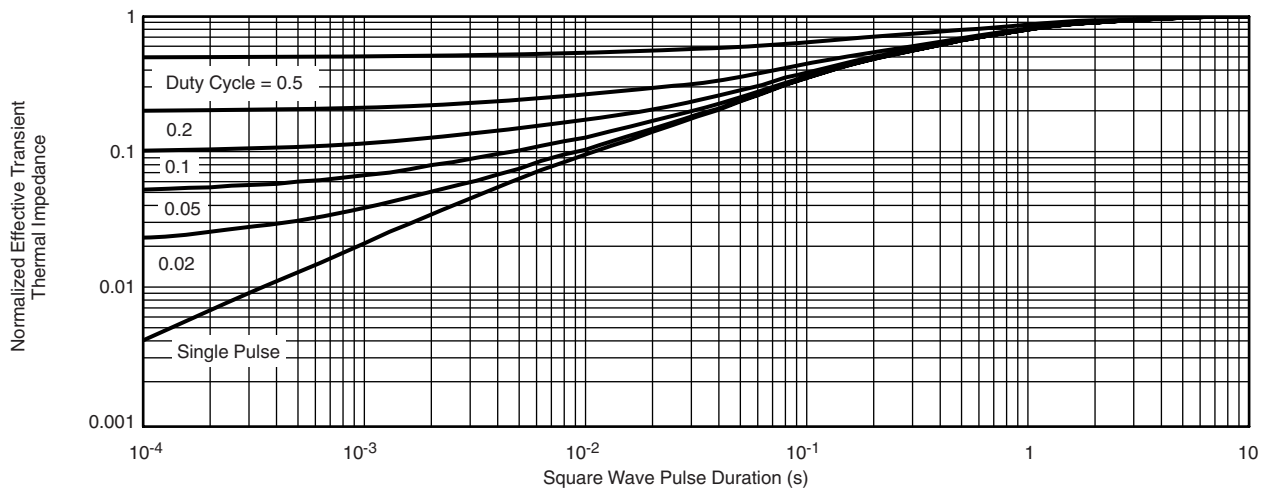


* The power dissipation P_D is based on $T_{J(max)} = 150\text{ °C}$, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit.

CHANNEL-2 TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



Normalized Thermal Transient Impedance, Junction-to-Ambient



Normalized Thermal Transient Impedance, Junction-to-Foot

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see www.vishay.com/ppg?70449.

SOIC (NARROW): 8-LEAD

JEDEC Part Number: MS-012



DIM	MILLIMETERS		INCHES	
	Min	Max	Min	Max
A	1.35	1.75	0.053	0.069
A ₁	0.10	0.20	0.004	0.008
B	0.35	0.51	0.014	0.020
C	0.19	0.25	0.0075	0.010
D	4.80	5.00	0.189	0.196
E	3.80	4.00	0.150	0.157
e	1.27 BSC		0.050 BSC	
H	5.80	6.20	0.228	0.244
h	0.25	0.50	0.010	0.020
L	0.50	0.93	0.020	0.037
q	0°	8°	0°	8°
S	0.44	0.64	0.018	0.026
ECN: C-06527-Rev. I, 11-Sep-06				
DWG: 5498				



Mounting LITTLE FOOT[®], SO-8 Power MOSFETs

Wharton McDaniel

Surface-mounted LITTLE FOOT power MOSFETs use integrated circuit and small-signal packages which have been modified to provide the heat transfer capabilities required by power devices. Leadframe materials and design, molding compounds, and die attach materials have been changed, while the footprint of the packages remains the same.

See Application Note 826, *Recommended Minimum Pad Patterns With Outline Drawing Access for Vishay Siliconix MOSFETs*, (<http://www.vishay.com/ppg?72286>), for the basis of the pad design for a LITTLE FOOT SO-8 power MOSFET. In converting this recommended minimum pad to the pad set for a power MOSFET, designers must make two connections: an electrical connection and a thermal connection, to draw heat away from the package.

In the case of the SO-8 package, the thermal connections are very simple. Pins 5, 6, 7, and 8 are the drain of the MOSFET for a single MOSFET package and are connected together. In a dual package, pins 5 and 6 are one drain, and pins 7 and 8 are the other drain. For a small-signal device or integrated circuit, typical connections would be made with traces that are 0.020 inches wide. Since the drain pins serve the additional function of providing the thermal connection to the package, this level of connection is inadequate. The total cross section of the copper may be adequate to carry the current required for the application, but it presents a large thermal impedance. Also, heat spreads in a circular fashion from the heat source. In this case the drain pins are the heat sources when looking at heat spread on the PC board.



Figure 1. Single MOSFET SO-8 Pad Pattern With Copper Spreading

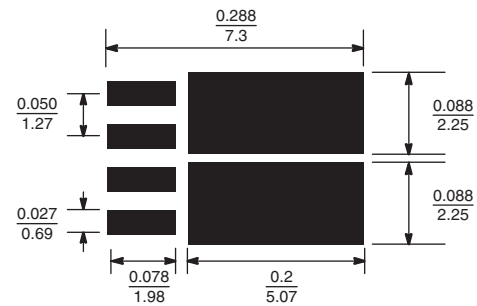


Figure 2. Dual MOSFET SO-8 Pad Pattern With Copper Spreading

The minimum recommended pad patterns for the single-MOSFET SO-8 with copper spreading (Figure 1) and dual-MOSFET SO-8 with copper spreading (Figure 2) show the starting point for utilizing the board area available for the heat-spreading copper. To create this pattern, a plane of copper overlies the drain pins. The copper plane connects the drain pins electrically, but more importantly provides planar copper to draw heat from the drain leads and start the process of spreading the heat so it can be dissipated into the ambient air. These patterns use all the available area underneath the body for this purpose.

Since surface-mounted packages are small, and reflow soldering is the most common way in which these are affixed to the PC board, “thermal” connections from the planar copper to the pads have not been used. Even if additional planar copper area is used, there should be no problems in the soldering process. The actual solder connections are defined by the solder mask openings. By combining the basic footprint with the copper plane on the drain pins, the solder mask generation occurs automatically.

A final item to keep in mind is the width of the power traces. The absolute minimum power trace width must be determined by the amount of current it has to carry. For thermal reasons, this minimum width should be at least 0.020 inches. The use of wide traces connected to the drain plane provides a low impedance path for heat to move away from the device.

RECOMMENDED MINIMUM PADS FOR SO-8



Recommended Minimum Pads
Dimensions in Inches/(mm)

[Return to Index](#)



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